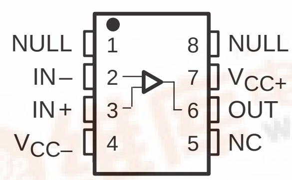
THS4061, THS4062
180-MHz HIGH-SPEED AMPLIFIERS

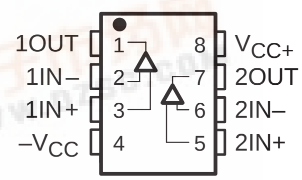
SLOS234D – DECEMBER 1998 – REVISED FEBRUARY 2000

- **High Speed**
  - **180 MHz Bandwidth (G = 1, –3 dB)**
  - **400 V/µs Slew Rate**
  - **40-ns Settling Time (0.1%)**
- **High Output Drive, I_O = 115 mA (typ)**
- **Excellent Video Performance**
  - **75 MHz 0.1 dB Bandwidth (G = 1)**
  - **0.02% Differential Gain**
  - **0.02° Differential Phase**
- **Very Low Distortion**
  - **THD = –72 dBc at f = 1 MHz**
- **Wide Range of Power Supplies**
  - **V_{CC} = ±5 V to ±15 V**
- **Available in Standard SOIC, MSOP PowerPAD™, JG, or FK Package**
- **Evaluation Module Available**

THS4061
JG, D AND DGN PACKAGE
(TOP VIEW)



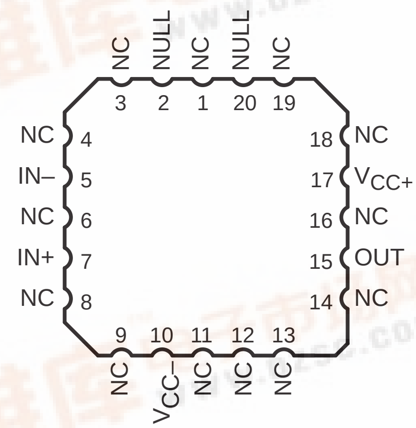
THS4062
D AND DGN PACKAGE
(TOP VIEW)



NC – No internal connection

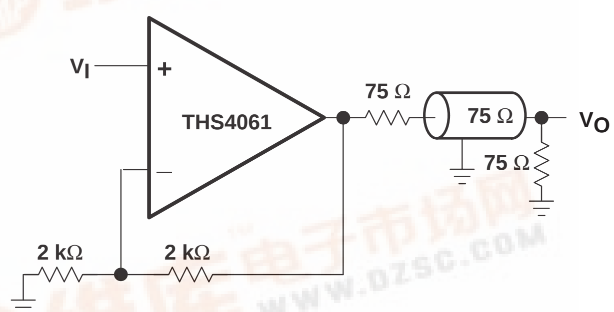
Cross-Section View Showing
PowerPAD Option (DGN)

THS4061
FK PACKAGE
(TOP VIEW)



description

The THS4061 and THS4062 are general-purpose, single/dual, high-speed voltage feedback amplifiers ideal for a wide range of applications including video, communication, and imaging. The devices offer very good ac performance with 180-MHz bandwidth, 400-V/µs slew rate, and 40-ns settling time (0.1%). The THS4061/2 are stable at all gains for both inverting and noninverting configurations. These amplifiers have a high output drive capability of 115 mA and draw only 7.8 mA supply current per channel. Excellent professional video results can be obtained with the low differential gain/phase errors of 0.02%/0.02° and wide 0.1 db flatness to 75 MHz. For applications requiring low distortion, the THS4061/2 is ideally suited with total harmonic distortion of –72 dBc at f = 1 MHz.



LINE DRIVER (G = 2)

CAUTION: The THS4061 and THS4062 provide ESD protection circuitry. However, permanent damage can still occur if this device is subjected to high-energy electrostatic discharges. Proper ESD precautions are recommended to avoid any performance degradation or loss of functionality

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Insruments Incorporated.

RELATED DEVICES	
DEVICE	**DESCRIPTION**
THS4011/2	290-MHz Low Distortion High-Speed Amplifiers
THS4031/2	100-MHz Low Noise High Speed-Amplifiers
THS4061/2	180-MHz High-Speed Amplifiers

AVAILABLE OPTIONS

T_A	NUMBER OF CHANNELS	PACKAGED DEVICES				MSOP SYMBOL	EVALUATION MODULES
		PLASTIC SMALL OUTLINE† (D)	PLASTIC MSOP† (DGN)	CERAMIC DIP (JG)	CHIP CARRIER (FK)		
0°C to 70°C	1	THS4061CD	THS4061CDGN	—	—	TIABS	THS4061EVM
	2	THS4062CD	THS4062CDGN	—	—	TIABM	THS4062EVM
–40°C to 85°C	1	THS4061ID	THS4061IDGN	—	—	TIABT	—
	2	THS4062ID	THS4062IDGN	—	—	TIABN	—
–55°C to 125°C	1	—	—	THS4061MJG	THS4061MFK	—	—

† The D and DGN packages are available taped and reeled. Add an R suffix to the device type (i.e., THS4061CDGNR).

functional block diagram

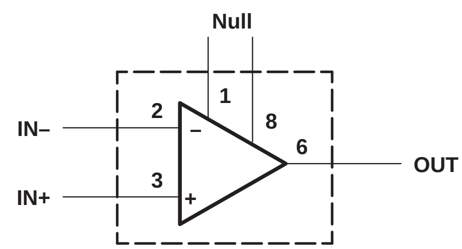


Figure 1. THS4061 – Single Channel

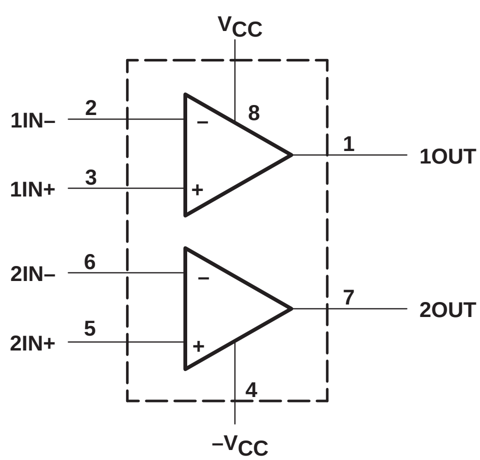


Figure 2. THS4062 – Dual Channel

absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage, $V_{CC}+$ to $V_{CC}-$ . . . . . 33 V
Input voltage, V_I . . . . . $\pm V_{CC}$
Output current, I_O . . . . . 150 mA
Differential input voltage, V_{IO} . . . . . ±4 V
Continuous total power dissipation . . . . . See Dissipation Rating Table
Maximum junction temperature, T_J . . . . . 150°C
Operating free-air temperature, T_A: C-suffix . . . . . 0°C to 70°C
I-suffix . . . . . –40°C to 85°C
M-suffix . . . . . –55°C to 125°C
Storage temperature, T_{stg} . . . . . –65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds, D and DGN package . . . . . 300°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds, JG package . . . . . 300°C
Case temperature for 60 seconds, FK package . . . . . 260°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	$T_A \le 25°C$ POWER RATING	DERATING FACTOR ABOVE $T_A = 25°C$	$T_A = 70°C$ POWER RATING	$T_A = 85°C$ POWER RATING	$T_A = 125°C$ POWER RATING
D	740 mW	6 mW/°C	475 mW	385 mW	—
DGN‡	2.14 W	17.1 mW/°C	1.37 W	1.11 W	—
JG	1057 mW	8.4 mW/°C	627 mW	546 mW	210 mW
FK	1375 mW	11 mW/°C	880 mW	715 mW	275 mW

‡ The DGN package incorporates a PowerPAD on the underside of the device. This acts as a heatsink and must be connected to a thermal dissipation plane for proper power dissipation. Failure to do so can result in exceeding the maximum specified junction temperature, which could permanently damage the device.

recommended operating conditions

		MIN	NOM	MAX	UNIT
Supply voltage, $V_{CC}+$ and $V_{CC}-$	Dual supply	±4.5		±16	V
	Single supply	9		32	
Operating free-air temperature, T_A	C-suffix	0		70	°C
	I-suffix	–40		85	
	M-suffix	–55		125	

electrical characteristics at T_A = 25°C, V_{CC} = ±15 V, R_L = 150 Ω (unless otherwise noted)

dynamic performance

PARAMETER		TEST CONDITIONS†		THS4061C/I, THS4062C/I MIN	TYP	MAX	UNIT
BW	Dynamic performance small-signal bandwidth (–3 dB)	V_{CC} = ±5 V	Gain = 1		180		MHz
		V_{CC} = ±15 V	Gain = –1		50		MHz
		V_{CC} = ±5 V			50		
	Bandwidth for 0.1 dB flatness	V_{CC} = ±15 V	Gain = 1		75		MHz
		V_{CC} = ±5 V			20		
SR	Slew rate	V_{CC} = ±15 V	Gain = –1		400		V/µs
		V_{CC} = ±5 V			350		
t_s	Settling time to 0.1%	V_{CC} = ±15 V, 5-V step (0 V to 5 V)	Gain = –1		40		ns
		V_{CC} = ±5 V, V_O = –2.5 V to 2.5 V,			40		
	Settling time to 0.01%	V_{CC} = ±15 V, 5-V step (0 V to 5 V)	Gain = –1		140		ns
		V_{CC} = ±5 V, V_O = –2.5 V to 2.5 V,			150		

† Full range = 0°C to 70°C for C suffix and –40°C to 85°C for I suffix

noise/distortion performance

PARAMETER		TEST CONDITIONS†		THS4061C/I, THS4062C/I MIN	TYP	MAX	UNIT
THD	Total harmonic distortion	f = 1 MHz			–72		dBc
V_n	Input voltage noise	f = 10 kHz, V_{CC} = ±5 V or ±15 V			14.5		nV/√Hz
I_n	Input current noise	f = 10 kHz, V_{CC} = ±5 V or ±15 V			1.6		pA/√Hz
	Differential gain error	Gain = 2, NTSC, 40 IRE modulation	V_{CC} = ±15 V		0.02 %		
			V_{CC} = ±5 V		0.02 %		
	Differential phase error	Gain = 2, NTSC, 40 IRE modulation	V_{CC} = ±15 V		0.02°		
			V_{CC} = ±5 V		0.06°		
	Channel-to-channel crosstalk (THS4062 only)	V_{CC} = ±5 V or ±15 V, f = 1 MHz			65		dB

† Full range = 0°C to 70°C for C suffix and –40°C to 85°C for I suffix

dc performance

PARAMETER		TEST CONDITIONS†		THS4061C/I, THS4062C/I MIN	TYP	MAX	UNIT
	Open loop gain	V_{CC} = ±15 V, V_O = ±10 V, R_L = 1 kΩ	T_A = 25°C	5	15		V/mV
			T_A = full range	4			
		V_{CC} = ±5 V, V_O = ±2.5 V, R_L = 1 kΩ	T_A = 25°C	2.5	8		V/mV
			T_A = full range	2			
V_{OS}	Input offset voltage	V_{CC} = ±5 V or ±15 V	T_A = full range		2.5	8	mV
	Offset drift	V_{CC} = ±5 V or ±15 V			15		µV/°C
I_{IB}	Input bias current	V_{CC} = ±5 V or ±15 V	T_A = full range		3	6	µA
I_{OS}	Input offset current	V_{CC} = ±5 V or ±15 V	T_A = full range		75	250	nA
	Offset current drift	T_A = full range			0.3		nA/°C

† Full range = 0°C to 70°C for C suffix and –40°C to 85°C for I suffix

electrical characteristics at $T_A = 25°C$, $V_{CC} = \pm15$ V, $R_L = 150\ \Omega$ (unless otherwise noted) (continued)

input characteristics

PARAMETER		TEST CONDITIONS†		THS4061C/I, THS4062C/I MIN	TYP	MAX	UNIT
V_{ICR}	Common-mode input voltage range	$V_{CC} = \pm15$ V		±13.8	±14.1		V
		$V_{CC} = \pm5$ V		±3.8	±4.3		
CMRR	Common mode rejection ratio	$V_{CC} = \pm15$ V, $V_{ICR} = \pm12$ V	T_A = full range	70	110		dB
		$V_{CC} = \pm5$ V, $V_{ICR} = \pm2.5$ V		70	95		
R_I	Input resistance				1		MΩ
C_i	Input capacitance				2		pF

† Full range = 0°C to 70°C for C suffix and –40°C to 85°C for I suffix

output characteristics

PARAMETER		TEST CONDITIONS†		THS4061C/I, THS4062C/I MIN	TYP	MAX	UNIT
V_O	Output voltage swing	$V_{CC} = \pm15$ V	$R_L = 250\ \Omega$	±11.5	±12.5		V
		$V_{CC} = \pm5$ V	$R_L = 150\ \Omega$	±3.2	±3.5		
		$V_{CC} = \pm15$ V	$R_L = 1\ k\Omega$	±13	±13.5		V
		$V_{CC} = \pm5$ V		±3.5	±3.7		
I_O	Output current	$V_{CC} = \pm15$ V	$R_L = 20\ \Omega$	80	115		mA
		$V_{CC} = \pm5$ V		50	75		
I_{SC}	Short-circuit current	$V_{CC} = \pm15$ V			150		mA
R_O	Output resistance	Open loop			12		Ω

† Full range = 0°C to 70°C for C suffix and –40°C to 85°C for I suffix

power supply

PARAMETER		TEST CONDITIONS†		THS4061C/I, THS4062C/I MIN	TYP	MAX	UNIT
V_{CC}	Supply voltage operating range	Dual supply		±4.5		±16.5	V
		Single supply		9		33	
I_{CC}	Quiescent current (per amplifier)	$V_{CC} = \pm15$ V	T_A = full range		7.8	10.5	mA
		$V_{CC} = \pm5$ V			7.3	10	
PSRR	Power supply rejection ratio	$V_{CC} = \pm5$ V or ±15 V	$T_A = 25°C$	70	78		dB
			T_A = full range	68			

† Full range = 0°C to 70°C for C suffix and –40°C to 85°C for I suffix

electrical characteristics at T_A = 25°C, V_{CC} = ±15 V, R_L = 150 Ω (unless otherwise noted)

dynamic performance

PARAMETER		TEST CONDITIONS†		THS4061M MIN	THS4061M TYP	THS4061M MAX	UNIT
BW	Unity-gain bandwidth	Closed loop, R_L = 1 kΩ	V_{CC} = ±15 V	*140	180		MHz
	Dynamic performance small-signal bandwidth (–3 dB)	V_{CC} = ±15 V	Gain = 1		180		MHz
		V_{CC} = ±5 V			180		
		V_{CC} = ±15 V	Gain = –1		50		MHz
		V_{CC} = ±5 V			50		
	Bandwidth for 0.1 dB flatness	V_{CC} = ±15 V	Gain = 1		75		MHz
		V_{CC} = ±5 V			20		
SR	Slew rate	V_{CC} = ±15 V R_L = 1 kΩ		*400	500		V/µs
t_s	Settling time to 0.1%	V_{CC} = ±15 V, 5-V step (0 V to 5 V)	Gain = –1		40		ns
		V_{CC} = ±5 V, V_O = –2.5 V to 2.5 V,			40		
	Settling time to 0.01%	V_{CC} = ±15 V, 5-V step (0 V to 5 V)	Gain = –1		140		ns
		V_{CC} = ±5 V, V_O = –2.5 V to 2.5 V,			150		

† Full range = –55°C to 125°C for M suffix
*This parameter is not tested.

noise/distortion performance

PARAMETER		TEST CONDITIONS†		THS4061M MIN	THS4061M TYP	THS4061M MAX	UNIT
THD	Total harmonic distortion	f = 1 MHz			–72		dBc
V_n	Input voltage noise	f = 10 kHz, V_{CC} = ±5 V or ±15 V			14.5		nV/√Hz
I_n	Input current noise	f = 10 kHz, V_{CC} = ±5 V or ±15 V			1.6		pA/√Hz
	Differential gain error	Gain = 2, NTSC, 40 IRE Modulation	V_{CC} = ±15 V		0.02		%
			V_{CC} = ±5 V		0.02		
	Differential phase error	Gain = 2, NTSC, 40 IRE Modulation	V_{CC} = ±15 V		0.02°		
			V_{CC} = ±5 V		0.06°		

† Full range = –55°C to 125°C for M suffix

dc performance

PARAMETER		TEST CONDITIONS†		THS4061M MIN	THS4061M TYP	THS4061M MAX	UNIT
	Open loop gain	V_{CC} = ±15 V, V_O = ±10 V, R_L = 1 kΩ	T_A = full range	5	9		V/mV
		V_{CC} = ±5 V, V_O = ±2.5 V, R_L = 1 kΩ		2.5	6		
V_{IO}	Input offset voltage	V_{CC} = ±5 V or ±15 V R_L = 1 kΩ	T_A = 25°C		2.5	8	mV
			T_A = full range			9	mV
	Offset drift	V_{CC} = ±5 V or ±15 V R_L = 1 kΩ	T_A = full range		15		µV/°C
I_{IB}	Input bias current	V_{CC} = ±5 V or ±15 V R_L = 1 kΩ	T_A = full range		3	6	µA
I_{IO}	Input offset current	V_{CC} = ±5 V or ±15 V R_L = 1 kΩ	T_A = full range		75	250	nA
	Offset current drift	V_{CC} = ±5 V or ±15 V R_L = 1 kΩ	T_A = full range		0.3		nA/°C

† Full range = –55°C to 125°C for M suffix

electrical characteristics at T_A = full range, V_{CC} = ±15 V, R_L = 1 kΩ (unless otherwise noted) (continued)

input characteristics

PARAMETER		TEST CONDITIONS†		THS4061M MIN	THS4061M TYP	THS4061M MAX	UNIT
V_{ICR}	Common-mode input voltage range	V_{CC} = ±15 V		±13.8	±14.1		V
		V_{CC} = ±5 V		±3.8	±4.3		
CMRR	Common mode rejection ratio	V_{CC} = ±15 V,	V_{ICR} = ±12 V	70	86		dB
		V_{CC} = ±5 V,	V_{ICR} = ±2.5 V	80	90		
R_I	Input resistance				1		MΩ
C_i	Input capacitance				2		pF

† Full range = –55°C to 125°C for M suffix

output characteristics

PARAMETER		TEST CONDITIONS†		THS4061M MIN	THS4061M TYP	THS4061M MAX	UNIT
V_O	Output voltage swing	V_{CC} = ±15 V	R_L = 250 Ω	±12	±13.1		V
		V_{CC} = ±5 V	R_L = 150 Ω	±3.2	±3.5		
		V_{CC} = ±15 V	R_L = 1 kΩ	±13	±13.5		V
		V_{CC} = ±5 V		±3.5	±3.7		
I_O	Output current	V_{CC} = ±15 V	R_L = 20 Ω	70	115		mA
		V_{CC} = ±5 V		50	75		
I_{SC}	Short-circuit current	V_{CC} = ±15 V	T_A = 25°C		150		mA
R_O	Output resistance	Open loop			12		Ω

† Full range = –55°C to 125°C for M suffix

power supply

PARAMETER		TEST CONDITIONS†		THS4061M MIN	THS4061M TYP	THS4061M MAX	UNIT
V_{CC}	Supply voltage operating range	Dual supply		±4.5		±16.5	V
		Single supply		9		33	
I_{CC}	Quiescent current	V_{CC} = ±15 V	T_A = 25°C		7.8	9	mA
		V_{CC} = ±5 V			7.3	8.5	
		V_{CC} = ±15 V	T_A = full range			11	
		V_{CC} = ±5 V				10.5	
PSRR	Power supply rejection ratio	V_{CC} = ±5 V or ±15 V	T_A = 25°C	76	80		dB
			T_A = full range	74	78		

† Full range = –55°C to 125°C for M suffix

TYPICAL CHARACTERISTICS

			FIGURE
I_{IB}	Input bias current	vs Free-air temperature	3
V_{IO}	Input offset voltage	vs Free-air temperature	4
	Open-loop gain	vs Frequency	5
	Phase	vs Frequency	5
	Differential gain	vs Number of loads	6, 8
	Differential phase	vs Number of loads	7, 9
	Closed-loop gain	vs Frequency	10, 11
	Output Amplitude	vs Frequency	12, 13
CMRR	Common-mode rejection ratio	vs Frequency	14
PSRR	Power-supply rejection ratio	vs Frequency	15
		vs Free-air temperature	16
$V_{O(PP)}$	Output voltage swing	vs Supply voltage	17
I_{CC}	Supply current	vs Free-air temperature	18
E_{nv}	Noise spectral density	vs Frequency	19
THD	Total harmonic distortion	vs Frequency	20, 21

TYPICAL CHARACTERISTICS

INPUT BIAS CURRENT
vs
FREE-AIR TEMPERATURE

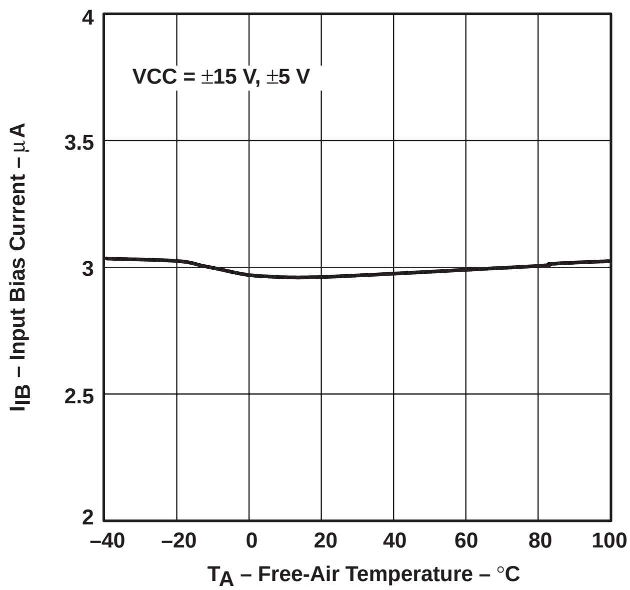


Figure 3

INPUT OFFSET VOLTAGE
vs
FREE-AIR TEMPERATURE

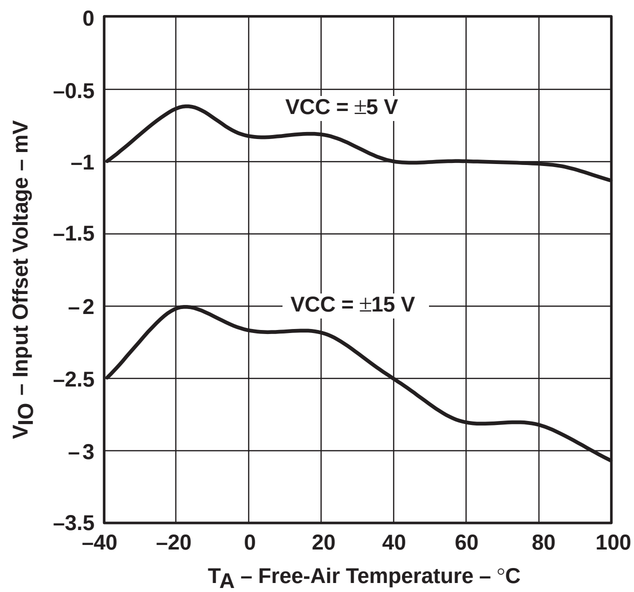


Figure 4

OPEN-LOOP GAIN AND PHASE
vs
FREQUENCY

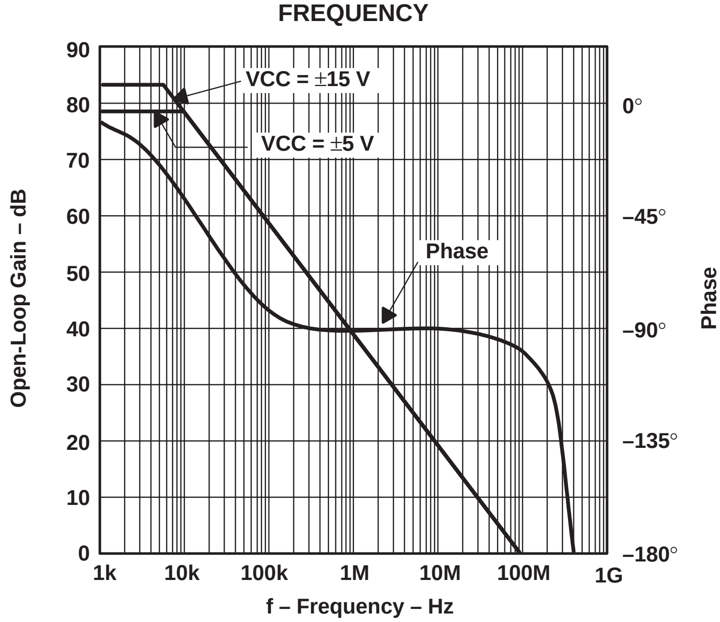


Figure 5

TYPICAL CHARACTERISTICS

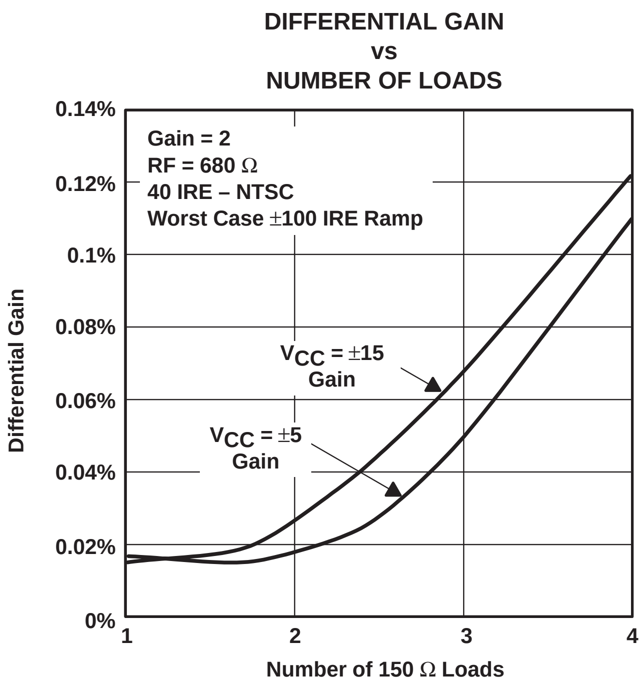


Figure 6

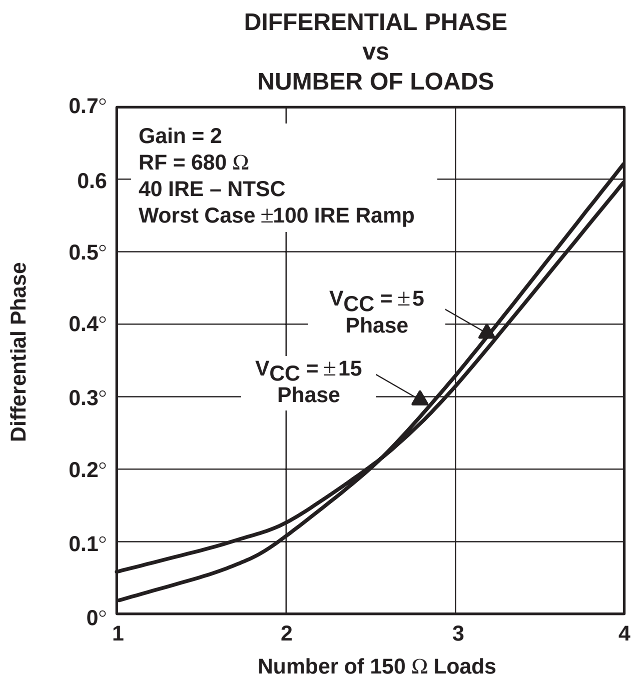


Figure 7

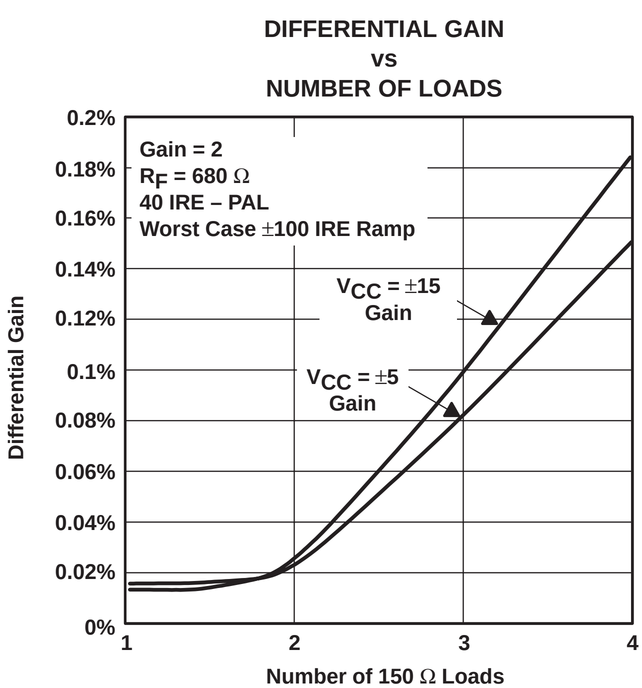


Figure 8

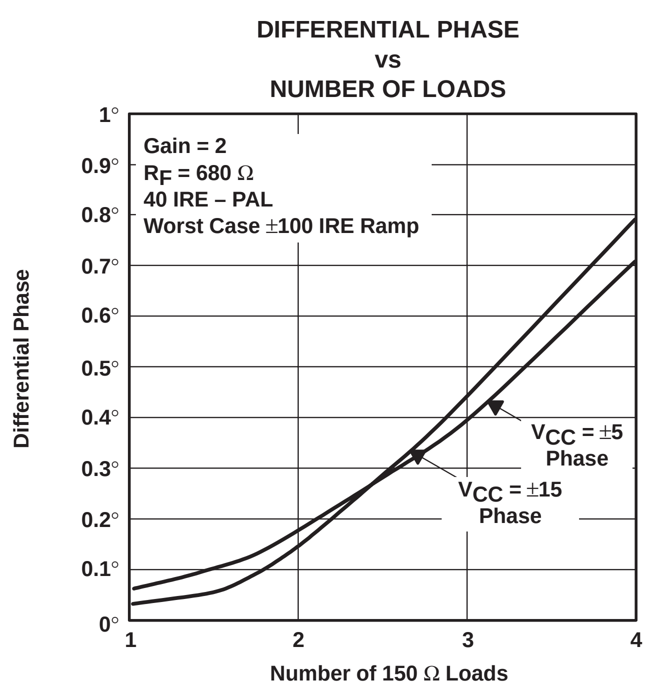


Figure 9

TYPICAL CHARACTERISTICS

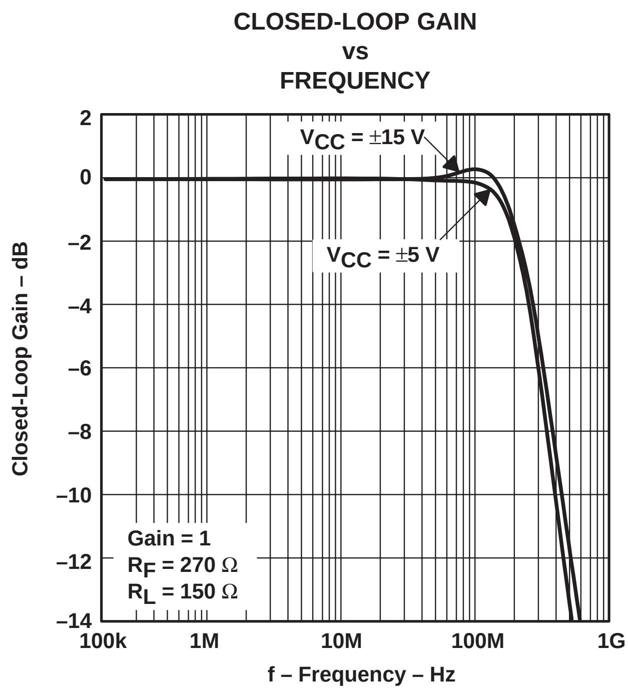


Figure 10

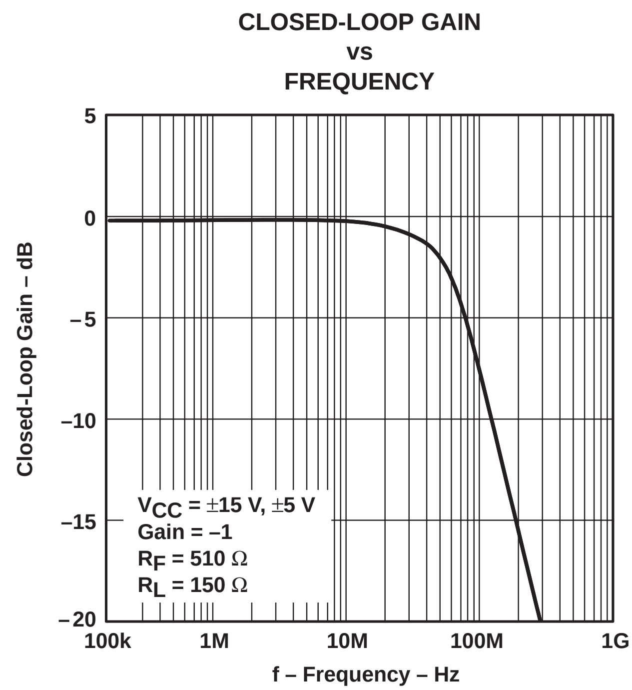


Figure 11

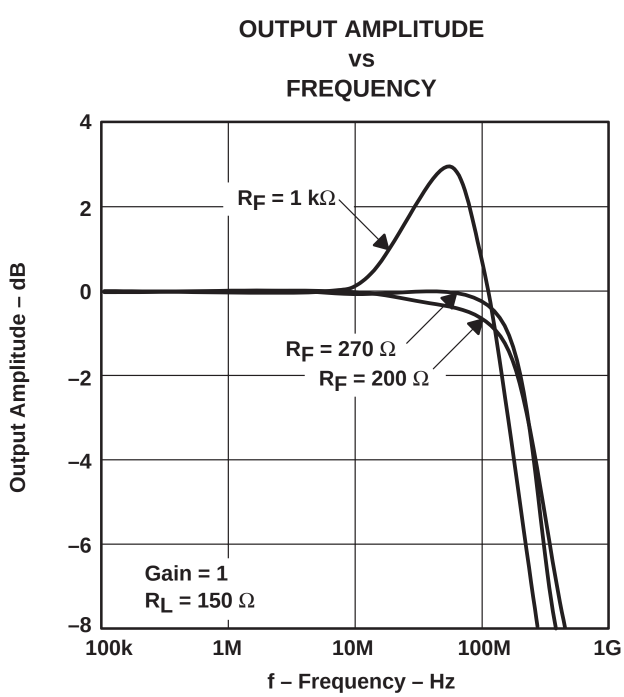


Figure 12

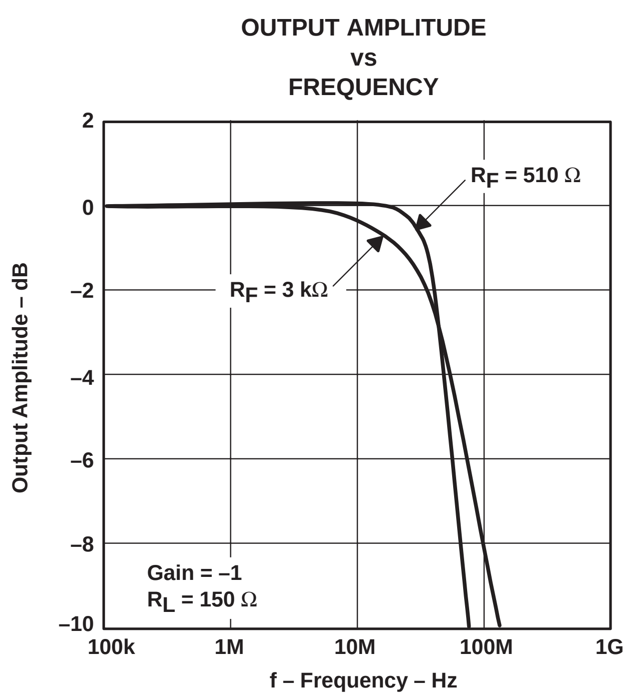


Figure 13

TYPICAL CHARACTERISTICS

COMMON-MODE REJECTION RATIO vs FREQUENCY

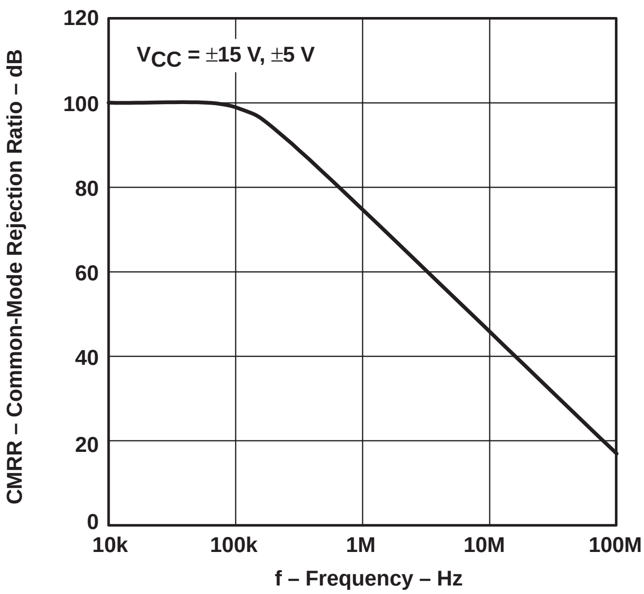


Figure 14

POWER SUPPLY REJECTION RATIO vs FREQUENCY

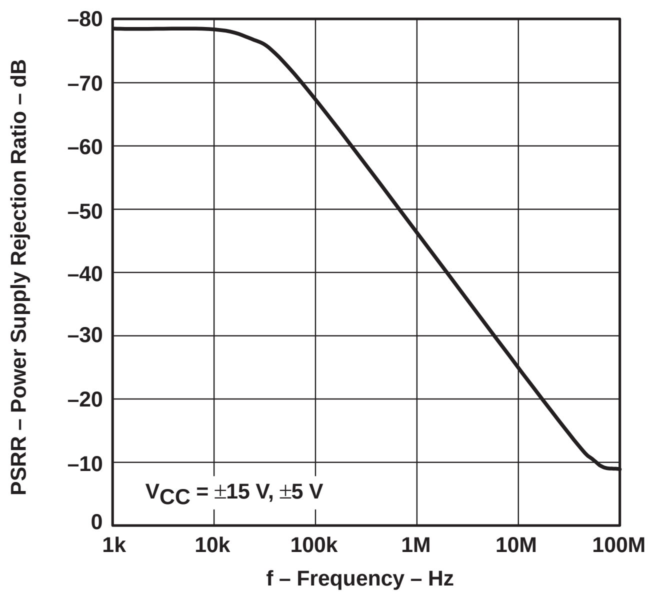


Figure 15

POWER SUPPLY REJECTION RATIO vs FREE-AIR TEMPERATURE

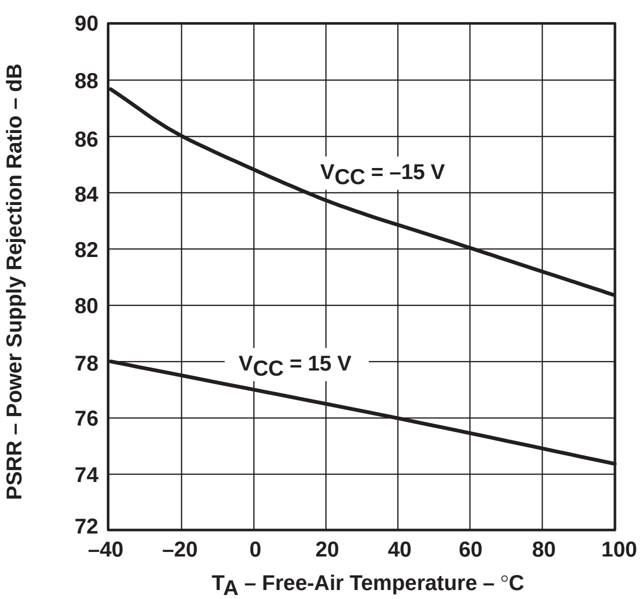


Figure 16

OUTPUT VOLTAGE SWING vs SUPPLY VOLTAGE

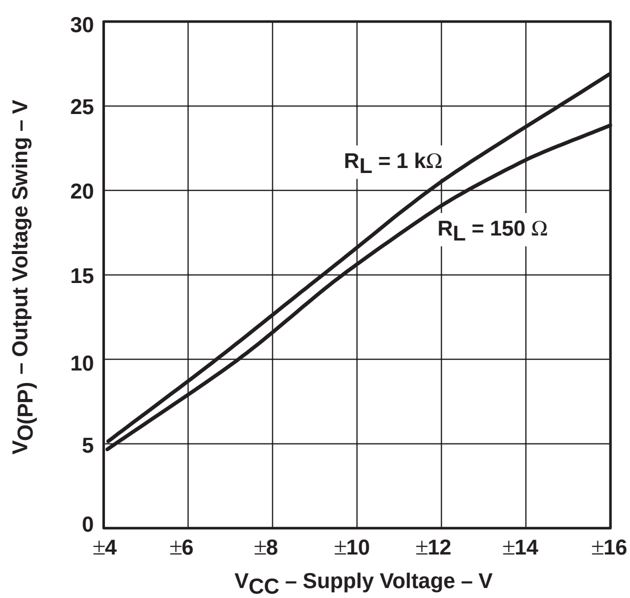


Figure 17

TYPICAL CHARACTERISTICS

SUPPLY CURRENT vs FREE-AIR TEMPERATURE

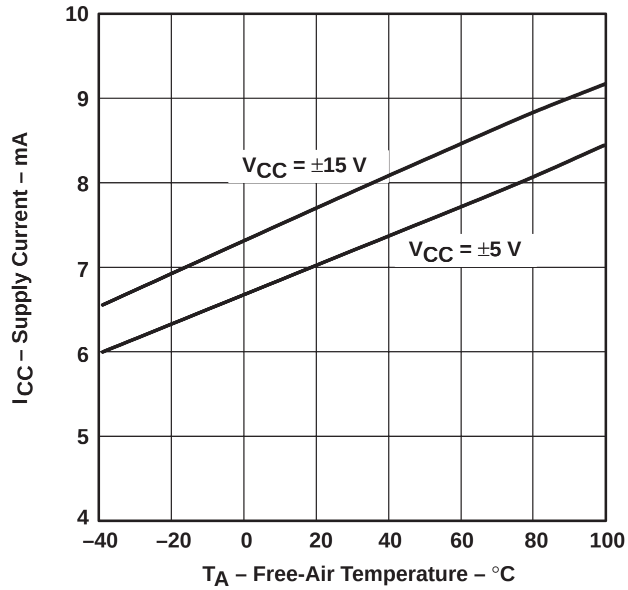


Figure 18

NOISE SPECTRAL DENSITY vs FREQUENCY

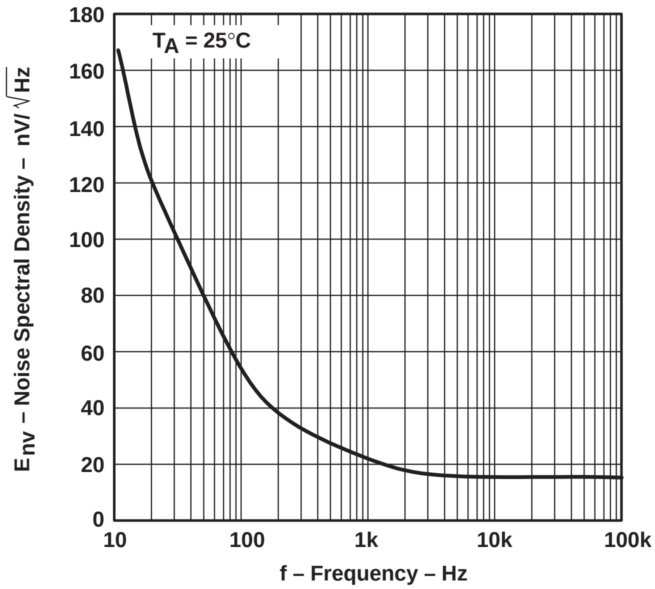


Figure 19

TOTAL HARMONIC DISTORTION vs FREQUENCY

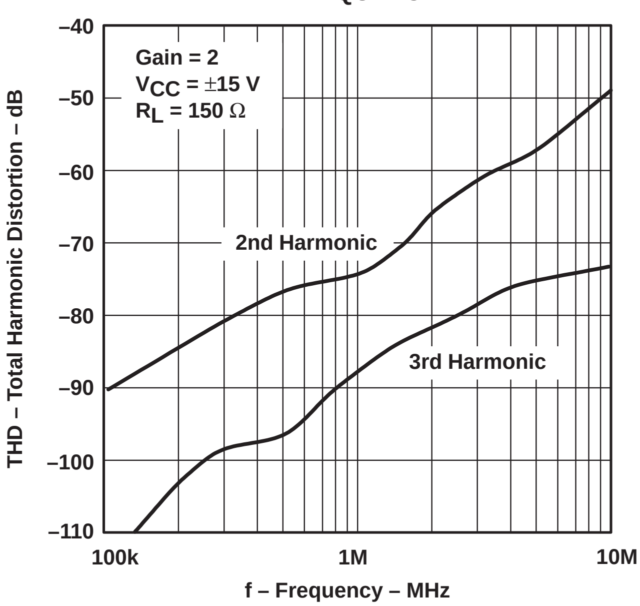


Figure 20

TOTAL HARMONIC DISTORTION vs FREQUENCY

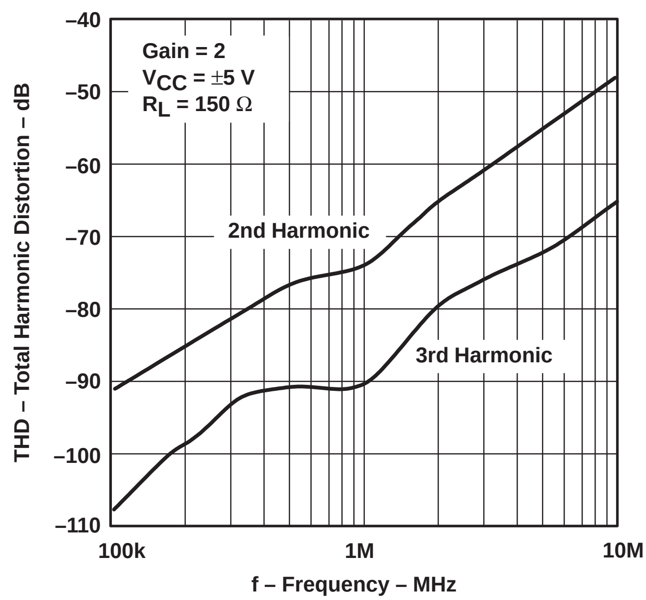


Figure 21

APPLICATION INFORMATION

theory of operation

The THS406x is a high speed, operational amplifier configured in a voltage feedback architecture. It is built using a 30-V, dielectrically isolated, complementary bipolar process with NPN and PNP transistors possessing f_Ts of several GHz. This results in an exceptionally high performance amplifier that has a wide bandwidth, high slew rate, fast settling time, and low distortion. A simplified schematic is shown in Figure 22.

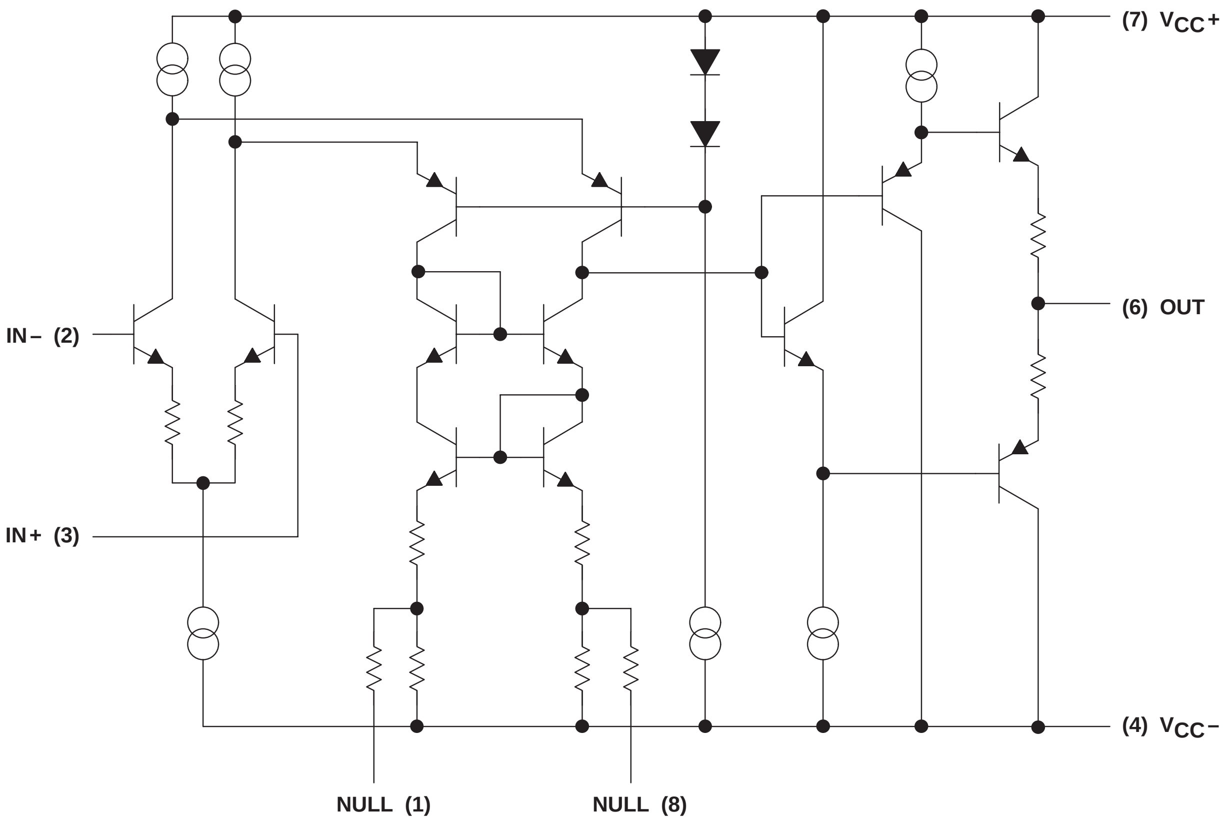


Figure 22. THS4061 Simplified Schematic

APPLICATION INFORMATION

offset nulling

The THS4061 has very low input offset voltage for a high-speed amplifier. However, if additional correction is required, an offset nulling function has been provided. By placing a potentiometer between terminals 1 and 8 and tying the wiper to the negative supply, the input offset can be adjusted. This is shown in Figure 23.

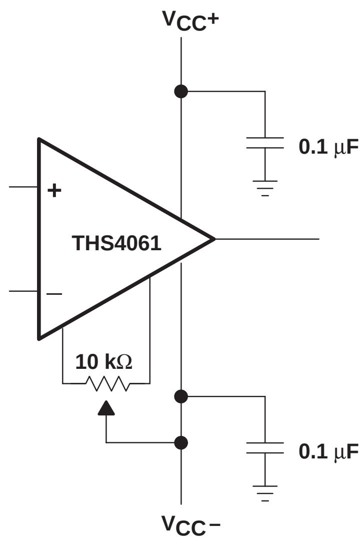


Figure 23. Offset Nulling Schematic

optimizing unity gain response

Internal frequency compensation of the THS406x was selected to provide very wideband performance yet still maintain stability when operated in a noninverting unity gain configuration. When amplifiers are compensated in this manner there is usually peaking in the closed loop response and some ringing in the step response for very fast input edges, depending upon the application. This is because a minimum phase margin is maintained for the G=+1 configuration. For optimum settling time and minimum ringing, a feedback resistor of 270 Ω should be used as shown in Figure 24. Additional capacitance can also be used in parallel with the feedback resistance if even finer optimization is required.

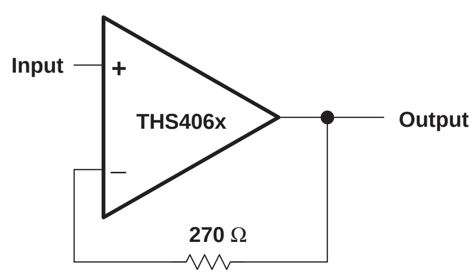


Figure 24. Noninverting, Unity Gain Schematic

APPLICATION INFORMATION

driving a capacitive load

Driving capacitive loads with high performance amplifiers is not a problem as long as certain precautions are taken. The first is to realize that the THS406x has been internally compensated to maximize its bandwidth and slew rate performance. When the amplifier is compensated in this manner, capacitive loading directly on the output will decrease the device's phase margin leading to high frequency ringing or oscillations. Therefore, for capacitive loads of greater than 10 pF, it is recommended that a resistor be placed in series with the output of the amplifier, as shown in Figure 25. A minimum value of 20 Ω should work well for most applications. For example, in 75-Ω transmission systems, setting the series resistor value to 75 Ω both isolates any capacitance loading and provides the proper line impedance matching at the source end.

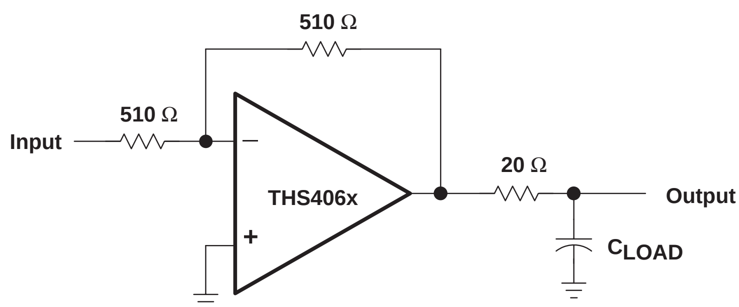


Figure 25. Driving a Capacitive Load

circuit layout considerations

In order to achieve the levels of high frequency performance of the THS406x, it is essential that proper printed-circuit board high frequency design techniques be followed. A general set of guidelines is given below. In addition, a THS406x evaluation board is available to use as a guide for layout or for evaluating the device performance.

- Ground planes – It is highly recommended that a ground plane be used on the board to provide all components with a low inductive ground connection. However, in the areas of the amplifier inputs and output, the ground plane can be removed to minimize the stray capacitance.
- Proper power supply decoupling – Use a 6.8-µF tantalum capacitor in parallel with a 0.1-µF ceramic capacitor on each supply terminal. It may be possible to share the tantalum among several amplifiers depending on the application, but a 0.1-µF ceramic capacitor should always be used on the supply terminal of every amplifier. In addition, the 0.1-µF capacitor should be placed as close as possible to the supply terminal. As this distances increases, the inductance in the connecting trace makes the capacitor less effective. The designer should strive for distances of less than 0.1 inches between the device power terminals and the ceramic capacitors.
- Sockets – Sockets are not recommended for high-speed operational amplifiers. The additional lead inductance in the socket pins will often lead to stability problems. Surface-mount packages soldered directly to the printed-circuit board is the best implementation.
- Short trace runs/compact part placements – Optimum high frequency performance is achieved when stray series inductance has been minimized. To realize this, the circuit layout should be made as compact as possible thereby minimizing the length of all trace runs. Particular attention should be paid to the inverting input of the amplifier. Its length should be kept as short as possible. This will help to minimize stray capacitance at the input of the amplifier.

APPLICATION INFORMATION

circuit layout considerations (continued)

- Surface-mount passive components – Using surface-mount passive components is recommended for high-frequency amplifier circuits for several reasons. First, because of the extremely low lead inductance of surface-mount components, the problem with stray series inductance is greatly reduced. Second, the small size of surface-mount components naturally leads to a more compact layout, thereby minimizing both stray inductance and capacitance. If leaded components are used, it is recommended that the lead lengths be kept as short as possible.

evaluation board

An evaluation board is available for the THS4061 (literature number SLOP226) and THS4062 (literaure number SLOP235). This board has been configured for very low parasitic capacitance in order to realize the full performance of the amplifier. A schematic of the evaluation board is shown in Figure 26. The circuitry has been designed so that the amplifier may be used in either an inverting or noninverting configuration. To order the evaluation board contact your local TI sales office or distributor. For more detailed information, refer to the *THS4061 EVM User's Manual* (literature number SLOU038) or the *THS4062 EVM User's Manual* (literature number SLOU040)

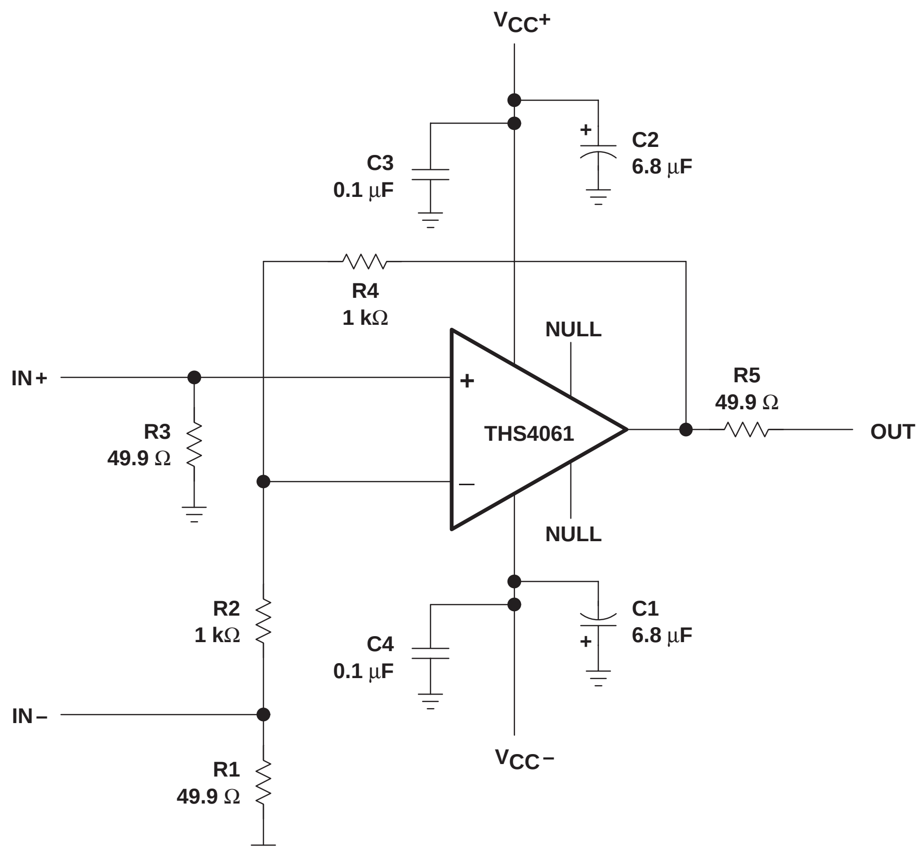
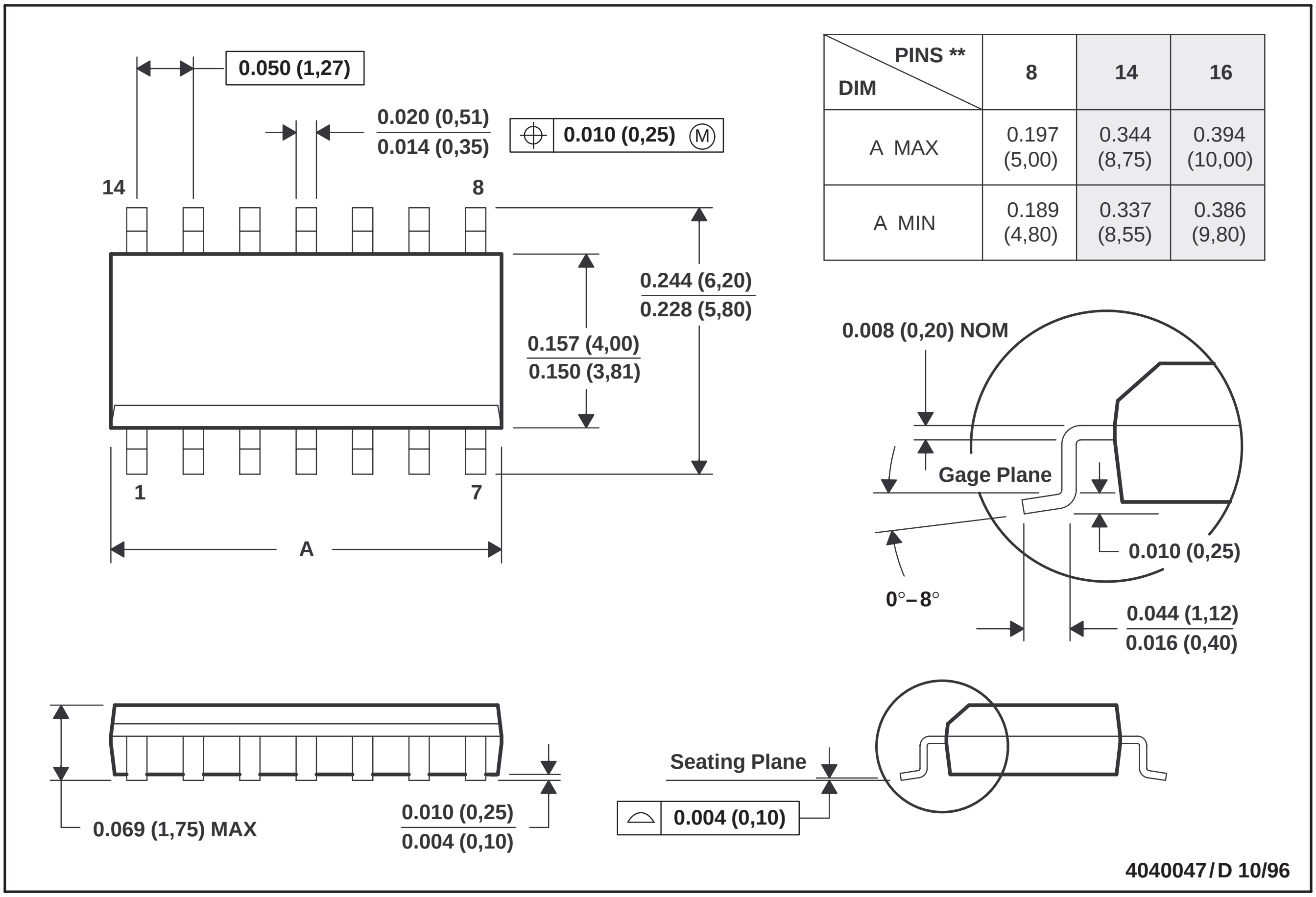


Figure 26. THS4061 Evaluation Board Schematic

MECHANICAL INFORMATION

D (R-PDSO-G)** **PLASTIC SMALL-OUTLINE PACKAGE**

14 PIN SHOWN

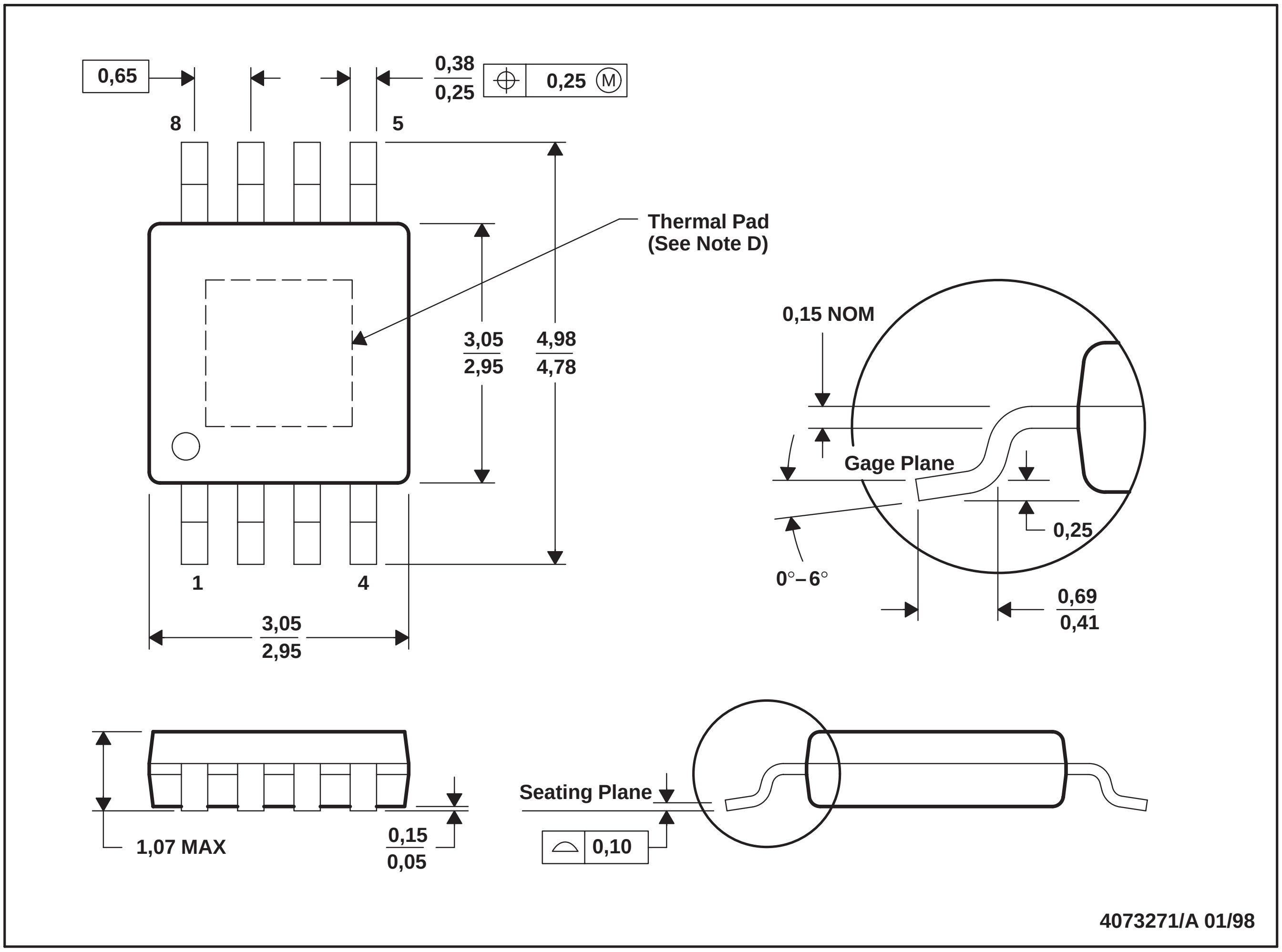


DIM \ PINS **	8	14	16
A MAX	0.197 (5,00)	0.344 (8,75)	0.394 (10,00)
A MIN	0.189 (4,80)	0.337 (8,55)	0.386 (9,80)

NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).
D. Falls within JEDEC MS-012

MECHANICAL INFORMATION

DGN (S-PDSO-G8) **PowerPAD™ PLASTIC SMALL-OUTLINE PACKAGE**

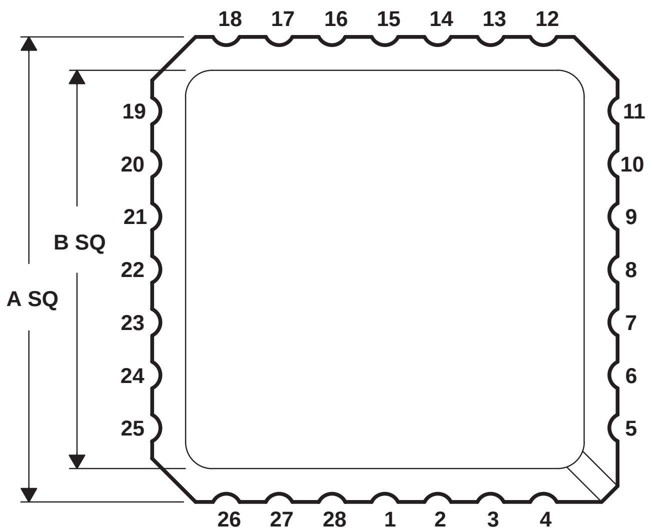


NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions include mold flash or protrusions.
D. The package thermal performance may be enhanced by attaching an external heat sink to the thermal pad. This pad is electrically and thermally connected to the backside of the die and possibly selected leads.
E. Falls within JEDEC MO-187

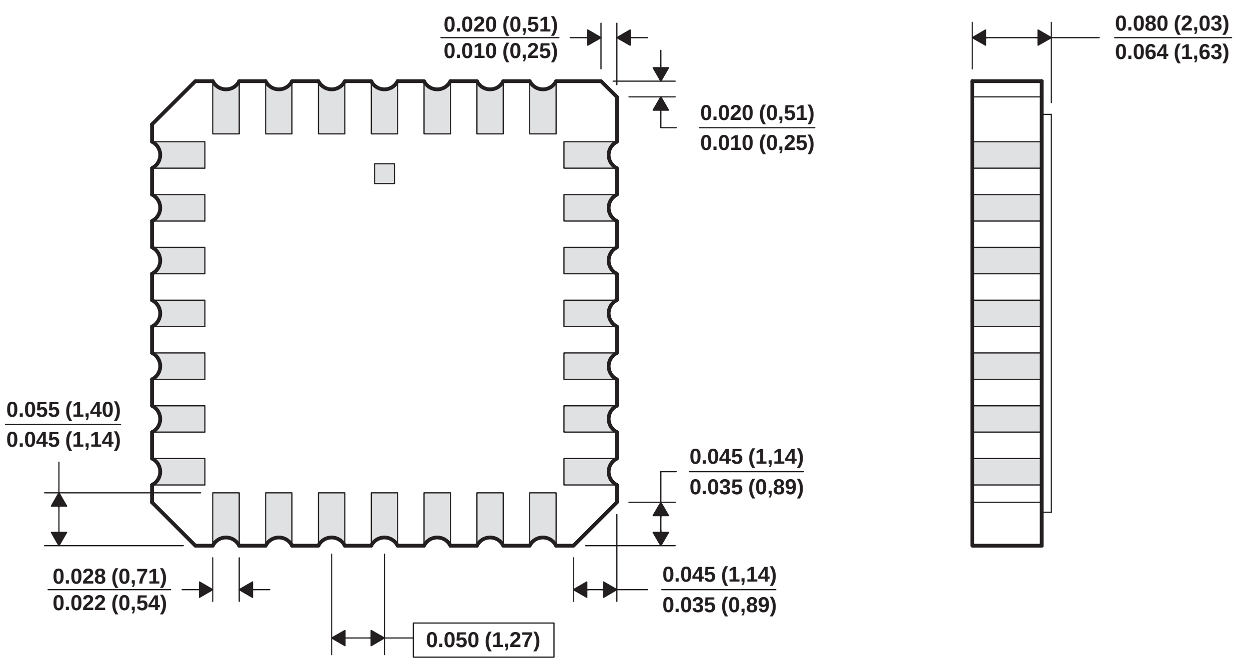
MECHANICAL INFORMATION

FK (S-CQCC-N)** **LEADLESS CERAMIC CHIP CARRIER**

28 TERMINAL SHOWN



NO. OF TERMINALS **	A		B	
	MIN	MAX	MIN	MAX
20	0.342 (8,69)	0.358 (9,09)	0.307 (7,80)	0.358 (9,09)
28	0.442 (11,23)	0.458 (11,63)	0.406 (10,31)	0.458 (11,63)
44	0.640 (16,26)	0.660 (16,76)	0.495 (12,58)	0.560 (14,22)
52	0.739 (18,78)	0.761 (19,32)	0.495 (12,58)	0.560 (14,22)
68	0.938 (23,83)	0.962 (24,43)	0.850 (21,6)	0.858 (21,8)
84	1.141 (28,99)	1.165 (29,59)	1.047 (26,6)	1.063 (27,0)



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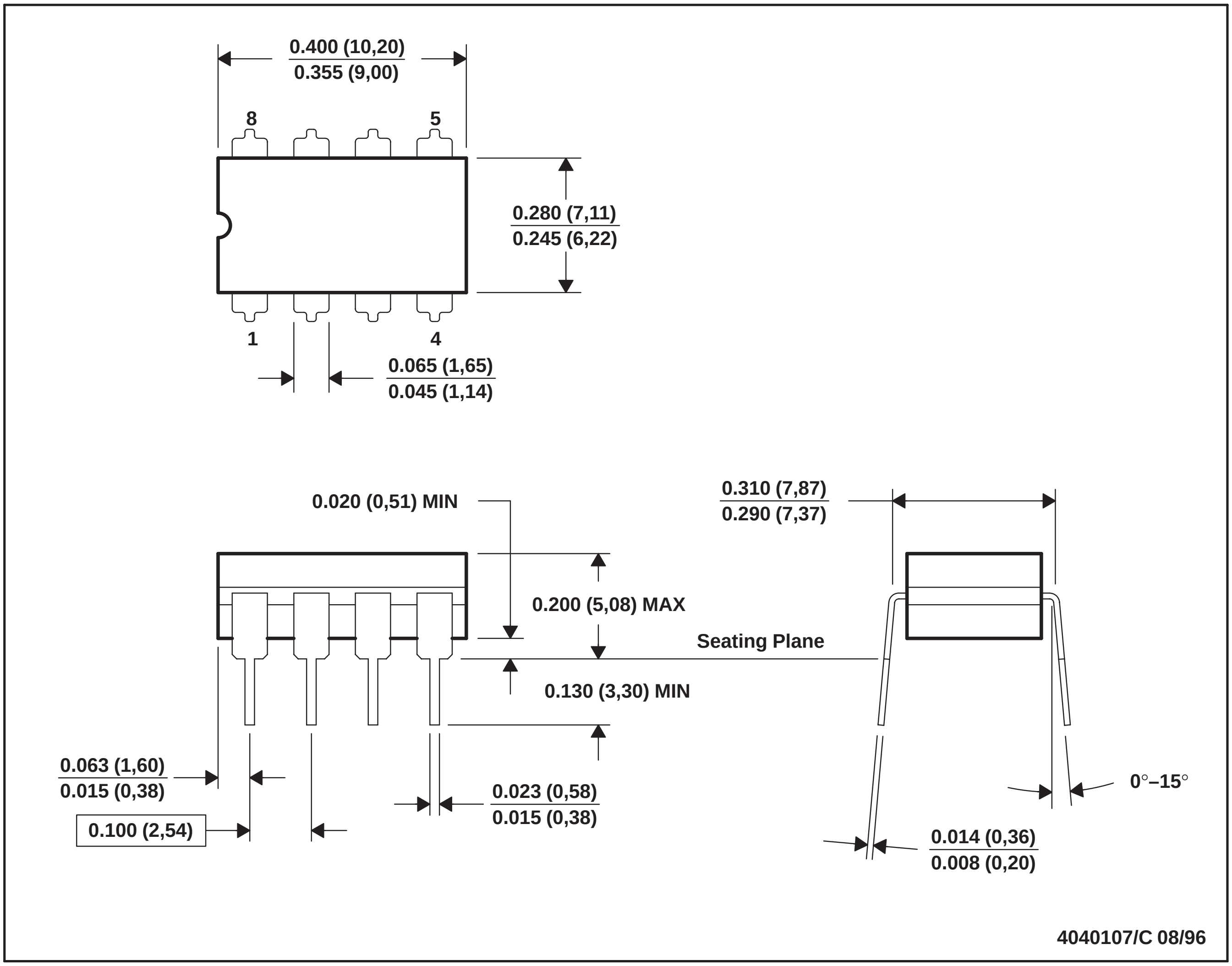
NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package can be hermetically sealed with a metal lid.
D. The terminals are gold plated.
E. Falls within JEDEC MS-004

MECHANICAL INFORMATION

JG (R-GDIP-T8) **CERAMIC DUAL-IN-LINE PACKAGE**



NOTES: A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. This package can be hermetically sealed with a ceramic lid using glass frit.
D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
E. Falls within MIL-STD-1835 GDIP1-T8

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